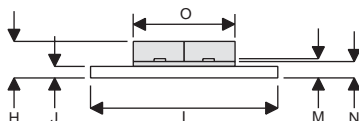
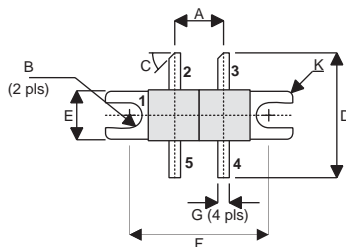


MECHANICAL DATA

**GOLD METALLISED  
MULTI-PURPOSE SILICON  
DMOS RF FET  
5W – 28V – 1GHz  
PUSH-PULL**



DK

PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1  
 PIN 3 DRAIN 2 PIN 4 GATE 2  
 PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
A	6.45	0.13	0.254	0.005
B	1.65R	0.13	0.065R	0.005
C	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
E	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
H	4.82	0.25	0.190	0.010
I	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
M	0.13	0.02	0.005	0.001
N	2.16	0.13	0.085	0.005

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 13 dB MINIMUM

APPLICATIONS

- VHF/UHF COMMUNICATIONS  
from DC to 1 GHz

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	35W
$BV_{DSS}$	Drain – Source Breakdown Voltage *	65V
$BV_{GSS}$	Gate – Source Breakdown Voltage *	$\pm 20V$
$I_{D(sat)}$	Drain Current *	1A
$T_{stg}$	Storage Temperature	$-65$ to $150^{\circ}C$
$T_j$	Maximum Operating Junction Temperature	$200^{\circ}C$

\* Per Side

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
<b>PER SIDE</b>						
B <sub>V</sub> DSS	Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0	I <sub>D</sub> = 10mA	65	V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 28V	V <sub>GS</sub> = 0	1	mA	
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> = 20V	V <sub>DS</sub> = 0	1	μA	
V <sub>GS(th)</sub>	Gate Threshold Voltage*	I <sub>D</sub> = 10mA	V <sub>DS</sub> = V <sub>GS</sub>	1	7	V
g <sub>fs</sub>	Forward Transconductance*	V <sub>DS</sub> = 10V	I <sub>D</sub> = 0.2A	0.18	S	
<b>TOTAL DEVICE</b>						
G <sub>PS</sub>	Common Source Power Gain	P <sub>O</sub> = 5W		13	dB	
η	Drain Efficiency	V <sub>DS</sub> = 28V	I <sub>DQ</sub> = 0.2A	40	%	
VSWR	Load Mismatch Tolerance	f = 1GHz		20:1	—	
<b>PER SIDE</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 28V	V <sub>GS</sub> = -5V f = 1MHz		12	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 28V	V <sub>GS</sub> = 0 f = 1MHz		6	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> = 28V	V <sub>GS</sub> = 0 f = 1MHz		0.5	pF

\* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

### HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

### THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 5.0°C / W
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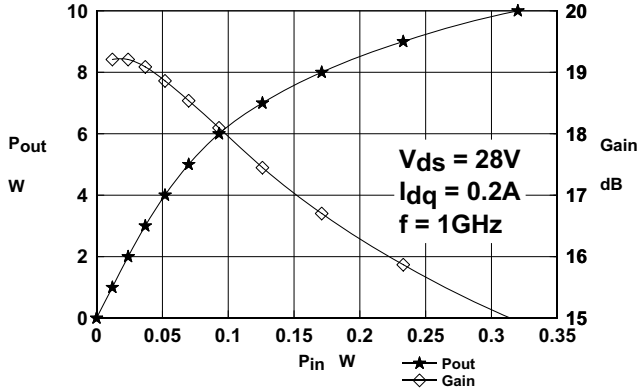


Figure 1 Output Power and Gain vs. Input power

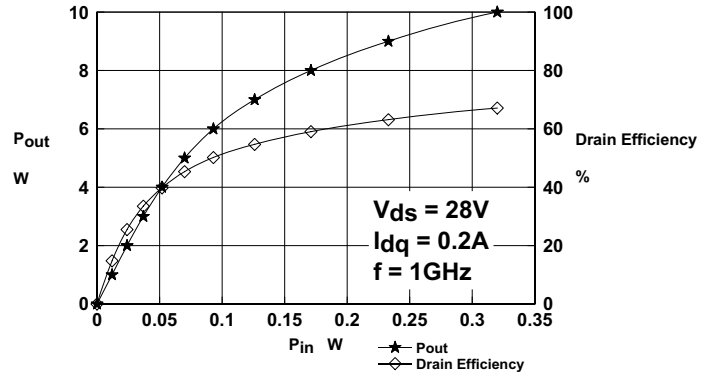


Figure 2 Output Power and Efficiency vs. Input Power

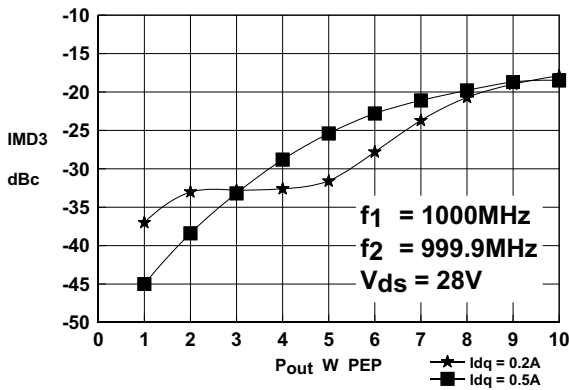


Figure 3 IMD Vs. Output Power.

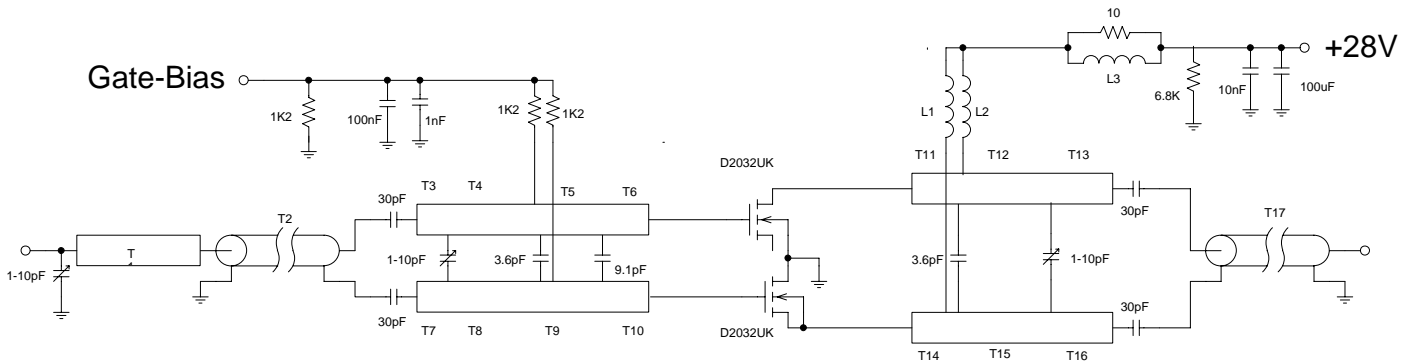
OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z <sub>S</sub> Ω	Z <sub>L</sub> Ω
1000MHz	1.1 - j2.5	5.1 - j17.1

Typical S Parameters

! Vds=28V, Idq=0.1A  
# MHz S MA R 50

!Freq !MHz	S11 mag ang	S21 mag ang	S12 mag ang	S22 mag ang
70	0.97 -36.4	15.8 156.6	0.017 67.2	0.91 -23.2
100	0.94 -48.0	14.1 146.3	0.021 58.1	0.88 -30.1
150	0.88 -65.3	12.3 129.9	0.027 45.5	0.81 -40.3
200	0.84 -78.5	10.2 114.7	0.029 34.8	0.77 -48.1
250	0.82 -88.4	8.8 106.0	0.029 28.1	0.75 -54.2
300	0.79 -97.1	7.7 98.3	0.029 27.3	0.73 -59.1
350	0.78 -105.5	6.9 88.5	0.028 22.2	0.72 -64.3
400	0.77 -113.3	6.0 84.5	0.026 24.2	0.71 -69.3
450	0.77 -121.8	5.4 77.8	0.024 23.3	0.70 -75.2
500	0.77 -128.9	4.9 75.3	0.022 29.6	0.70 -80.4
550	0.78 -136.7	4.6 68.3	0.020 35.0	0.70 -86.5
600	0.78 -144.0	4.4 65.4	0.020 46.6	0.70 -93.6
650	0.78 -150.8	4.0 57.2	0.020 57.6	0.70 -99.6
700	0.79 -156.7	3.7 52.3	0.022 68.5	0.71 -105.8
750	0.79 -160.9	3.4 46.7	0.025 76.6	0.70 -111.3
800	0.78 -164.2	3.0 41.4	0.028 81.6	0.69 -115.6
850	0.78 -166.3	2.7 39.5	0.032 87.8	0.68 -117.0
900	0.79 -168.5	2.6 38.4	0.036 92.3	0.68 -119.3
950	0.78 -170.3	2.5 36.8	0.044 97.4	0.70 -121.0
1000	0.79 -172.5	2.4 33.0	0.053 97.4	0.70 -124.2



## 1000MHz TEST FIXTURE

Substrate 0.8mm thick PTFE/glass  
 All microstrip lines  $W = 2.7\text{mm}$

T1	15.7
T2, T17	45mm 50 OHM UT 34 semi-rigid coax
T3, T7	7mm
T4, T8	15mm
T5, T9	7.6mm
T6, T10	8mm
T11, T14	8mm
T12, T15	11.2mm
T13, T16	7mm
L1, L2	6 turns 24swg enamelled copper wire, 3mm i.d.
L3	1.5 turn 24swg enamelled copper wire on Siemens B62152-A7X 2 hole core